

# Comparator Design Optimization

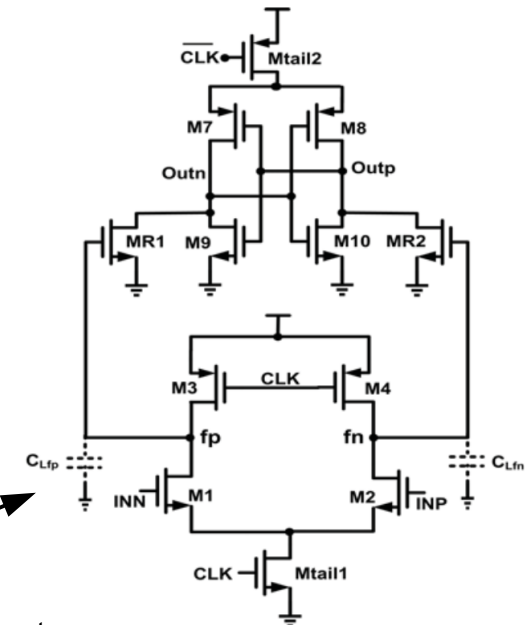
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# Three Designs

- Three Designs
  - Double-tail Comparator 1 (“DTC1”)
  - Single-phase DTC (Chen-Kai’s design)
  - Double-regenerative DTC (“DTC2”) (new design)
- Transistor-level Optimization
- Testbench
- Performance Comparison
- Summary of Design Tradeoffs

# Double Tail Comp. 1

- The “original” double-tail design
- CLK=0 → Pre-charge capacitance on nodes fn and fp to VDD
- CLK=1 → fn and fp discharge
- During discharge:  $|V_{fp} - V_{fn}|(t) \propto \frac{\Delta V_{IN} \times g_{m1,2} \times t}{C_{fp,n}}$
- Input with the lesser voltage discharges first → its respective output goes to zero on the second-stage x-inverter.



Symbolic capacitor; not a lumped component...

# Single-Phase DTC

- Structurally similar to DTC1; same theory of operation
- $\overline{\text{CLK}}$  is replaced with one additional PMOS & NMOS
- The additional NMOS & PMOS equate to an effective gm boost of  $2x \sim 3x$  in the second stage  
→  $2x \sim 3x$  faster response time

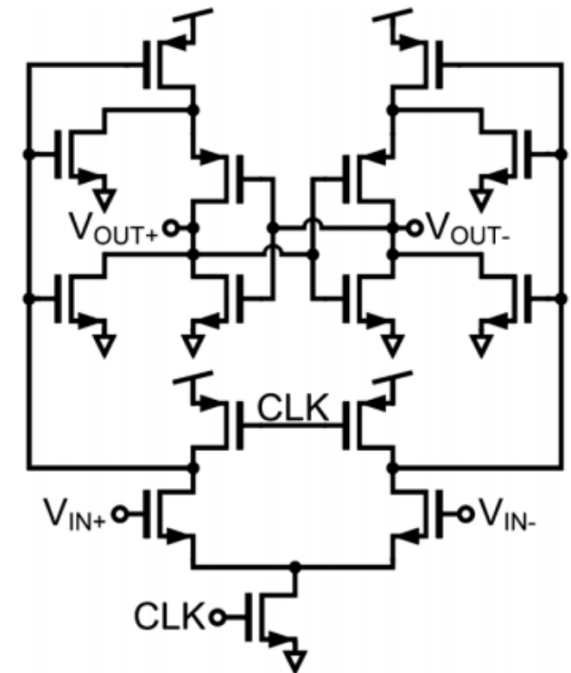
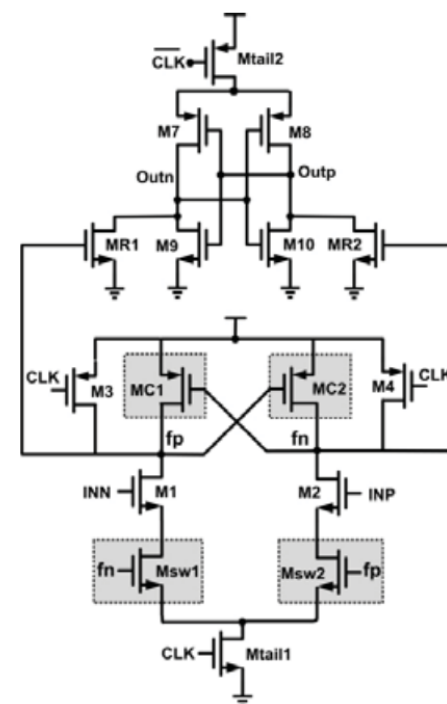


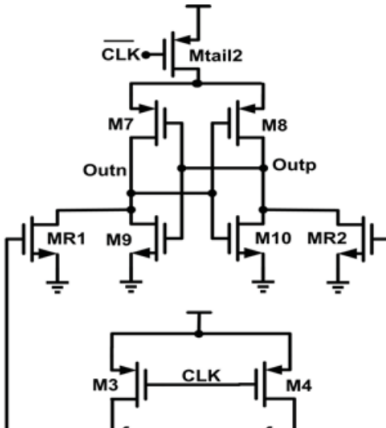
Figure from [2]

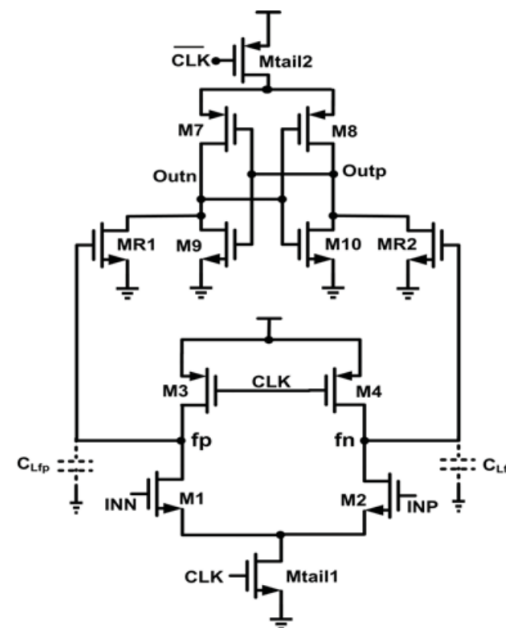
- Design proposed in [1]
- First stage is replaced with a regenerative stage
- Unlike the original DTC,  $V_{fn}$  and  $V_{fp}$  discharge rate is **exponential**

$$\{|V_{\text{fp}} - V_{\text{fn}}|\}(t) \propto \Delta V_{\text{IN}} \exp\left(\frac{g_{m1,2} \times t}{C_{\text{fp},n}}\right)$$

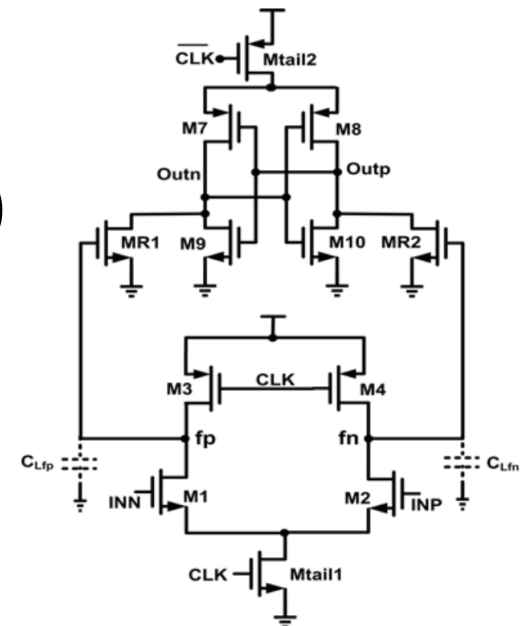
- $M_{sw1}$  &  $M_{sw2}$  used to avoid static DC flow



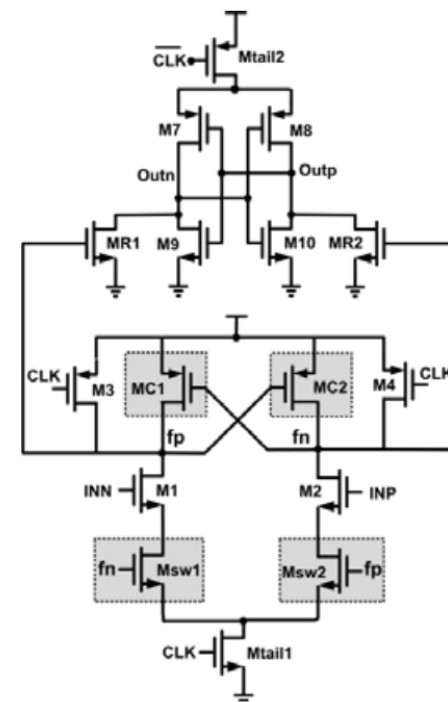
- First stage:
    - Larger  $M1, M2 \rightarrow$  faster decision time but more power
    - If discharge rate is too high  $\rightarrow$  risk of false latching (high noise); inadequate  $\{|V_{fp} - V_{fn}|\}$
  - Large  $M_{tail1}, M_{tail2} \rightarrow$  low  $V_{DS,ON}$
  - Don't use min length for analog transistors ( $L = 130$  nm)
  - Even number of fingers & multiplier for easier matching in layout (pref.  $m=8$ )
- 
- The diagram shows a differential pair circuit. At the top, a PMOS tail transistor  $M_{tail2}$  is connected to a common clock signal  $\overline{CLK}$ . Its source is connected to the sources of two PMOS transistors  $M7$  and  $M8$ . The gates of  $M7$  and  $M8$  are connected to a common clock signal  $CLK$ . The drains of  $M7$  and  $M8$  are connected to the gates of two NMOS transistors  $M9$  and  $M10$ . The sources of  $M9$  and  $M10$  are connected to ground. The gates of  $M9$  and  $M10$  are connected to a common clock signal  $CLK$ . The drains of  $M9$  and  $M10$  are connected to the sources of two PMOS transistors  $MR1$  and  $MR2$ . The gates of  $MR1$  and  $MR2$  are connected to a common clock signal  $CLK$ . The drains of  $MR1$  and  $MR2$  are connected to ground. The outputs of the circuit are  $Outn$  and  $Outp$ , which are the drains of  $M7$  and  $M8$  respectively.



- Second stage:
  - Min size inverters  $\rightarrow$  low cross-over power consumption
  - $g_{mR1} > g_{m9}$  and  $g_{mR2} > g_{m10}$  for stronger sensitivity to positive feedback, but slower response time
  - Large  $C_{fp,n} \rightarrow$  less noise; less false latching, but slower response time (higher time const., lower  $kT/C$  noise)
- Buffer on Outn and Outp to prevent perturbing the positive feedback on the min-size inverters



- First stage:
  - Regeneration in 1<sup>st</sup> stage → allows larger M1 & M2 (for less false-latching, faster response time, etc) without as much of a power penalty
  - Weaker MC1 & MC2, but stronger Msw1 & Msw2 → keeps power low
- Second stage:
  - $g_{mR1}$  and  $g_{mR2}$  need not to be as large due to exponential growth
  - MR1 & MR2 now mostly determined by max. false-latching (noise) spec.
  - Move most of  $C_{fp,n}$  to M3 and M4
  - Faster response time





- CLK: 320 MHz, 1000 cycles
- $V_{IN+} = 600.0\text{mV}$ ;  $V_{IN-} = 600.4\text{ mV}$  (recall  $1\text{LSB} \approx 977\text{ uV}$ )
- Two min-sized inverters (buffer) placed on each output
- 5 fF load on each output
- Transient sim, conservative accuracy, trans. Noise
  - $F_{\min} = 1\text{ Hz}$ ,  $F_{\max} = 100\text{ GHz}$ , Seed = 1, Scale = 1
- Input-referred noise spec [3]:

$$P[\text{Incorrect}] = \text{erfc} \left( \frac{\Delta V_{\text{IN}}}{\sigma \sqrt{2}} \right)$$



	DTC1	Single-phase DTC (Chen-Kai's design)	Double-Regen (DTC2)
<b>Avg. Power @ 320 MHz</b>	103.5 $\mu$ W	78.83 $\mu$ W	102.3 $\mu$ W
<b>Prop. Delay <math>t_{CLK \rightarrow OUT}</math></b>	210 pS	130 pS	127 pS
<b>P[correct] n=1000</b>	96.6 %	91.9 %	96.5 %
			97.2 % @ 120 $\mu$ W
<b>Input-referred <math>\sigma</math> ("input-ref. noise")</b>	189 $\mu$ V	229 $\mu$ V	190 $\mu$ V
<b><math>\Sigma C_{fn}</math></b>	98.178 fF	24.07 fF	69.37 fF
<b>Input transistor gate area (pre-layout), per transistor</b>	1.04 $\mu$ m <sup>2</sup> L = 130 nm	2.88 $\mu$ m <sup>2</sup> L = 60 nm	4.16 $\mu$ m <sup>2</sup> L = 130 nm

# Summary

- DTC1 has too many trade-offs relying on a few transistors
- Adding regenerative first stage allows for more flexibility
  - More transistors to play around with...
  - Exponential growth, as opposed to linear, in first stage eases second stage requirements
- Can be optimized even further for a single parameter instead of overall performance...

- Monte Carlo/corner simulations
- Further optimization?
- Optimization of other ADC components?
- Design of reference buffer
- Start layout (w/ Chen-Kai)
- Things to think about:
  - Layout: use of waffle/annular ring transistors for rad-hardness?
  - Fail-safe/redundancy circuitry to mitigate SEE/SEU's?
  - Additional circuits to fit into tapeout to study SEE/SEU? (probably not ADC related)

1. S. B. Mashhadi and R. Lotfi, "Analysis and Design of a Low-Voltage Low-Power Double-Tail Comparator," **IEEE Trans. On VLSI**, Vol. 22, No. 2, February 2014
2. Y. Lim and M.P. Flynn, "A 1mW 71.5dB SNDR 50 MS/S 13b fully differential ring-amplifier-based SAR-assisted pipeline ADC," in **Proc. IEEE ISSCC. Dig. Tech. Papers**, Feb. 2015, pp. 1–3.
3. <https://everynanocounts.com/2013/06/25/noise-effect-on-the-probability-of-comparator-decision/>